

1765
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: E. Morita

Serial No.: 09/726,860

Filed: November 30, 2000

For: METHOD OF MANUFACTURING
CRYSTAL OF III-V COMPOUND OF THE
NITRIDE SYSTEM, CRYSTAL
SUBSTRATE OF III-V COMPOUND OF
THE NITRIDE SYSTEM, CRYSTAL FILM
OF III-V COMPOUND OF THE NITRIDE
SYSTEM, AND METHOD OF
MANUFACTURING DEVICE

Case No.: 9792909-4715

Examiner: M. Anderson

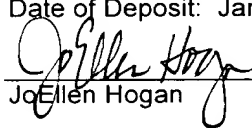
Group Art Unit: 1765

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Jo Ellen Hogan1/2/02
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Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Enclosed herewith is a Response to Restriction Requirement and
Supplemental Preliminary Amendment of E. Morita in the above-identified patent
application.

Also enclosed are: Return Receipt Postcard

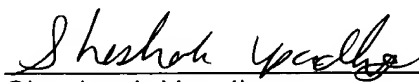
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Respectfully submitted,

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In the United States Patent and Trademark Office

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Inventor: E. Morita

Examiner: M. Anderson

Serial No.: 09/726,860

Group Unit: 1765

Title: Method of Manufacturing Crystal...

Atty. Docket No. 9792909-4715

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Response to Restriction Requirement and Supplemental Preliminary Amendment

In response to the Office Action dated, 03 Dec. 2001, requiring restriction of the claims, the applicant responds as follows.

A. In the Claims

Applicant provisionally elects Group I - corresponding to claims 1 to 16, drawn to the method.

Please cancel, without prejudice, claims 17-30 drawn to the substrate product.

Please also amend claims 1 to 16 as follows.

1. (Amended) A method of manufacturing a crystal of a III-V compound of the nitride system, the method including:

a first growth step [of forming] to form a first crystal layer, the first crystal layer further having a surface, by growing a crystal of a III-V compound of the nitride system on [the] a surface of a basal body;

a first mask forming step [of forming] to form a first mask pattern on the surface of the first crystal layer;